NSN 5961-01-022-7559

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-022-7559 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 25.0 repetitive peak reverse voltage **Current Rating Per Characteristic:** 25.00 amperes forward current, average of standard range **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Small terminal gate connected and large terminal cathode connected; junction pattern arrangement: npnp **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: